**Preferred Device** 

# **JFET Transistor**

# **N-Channel**

#### **Features**

• Pb-Free Package is Available

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain-Gate Voltage	$V_{DG}$	25	Vdc
Reverse Gate-Source Voltage	V <sub>GS(r)</sub>	25	Vdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Continuous Device Dissipation at or Below T <sub>C</sub> = 25°C Linear Derating Factor	P <sub>D</sub>	200 2.8	mW mW/°C
Storage Channel Temperature Range	T <sub>stg</sub>	-65 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

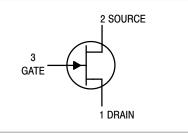
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.



# ON Semiconductor®

#### http://onsemi.com





SOT-23 (TO-236) CASE 318 STYLE 10

#### **MARKING DIAGRAM**



M6B = Device Code
M = Date Code\*
= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MMBF5484LT1	SOT-23	3,000 / Tape & Reel
MMBF5484LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

**Preferred** devices are recommended choices for future use and best overall value.

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate–Source Breakdown Voltage ( $I_G = -1.0 \mu Adc, V_{DS} = 0$ )	V <sub>(BR)GSS</sub>	-25	_	Vdc
Gate Reverse Current $(V_{GS} = -20 \text{ Vdc}, V_{DS} = 0)$ $(V_{GS} = -20 \text{ Vdc}, V_{DS} = 0, T_A = 100^{\circ}\text{C})$	I <sub>GSS</sub>	-	-1.0 -0.2	nAdc μAdc
Gate Source Cutoff Voltage (V <sub>DS</sub> = 15 Vdc, I <sub>D</sub> = 10 nAdc)	V <sub>GS(off)</sub>	-0.3	-3.0	Vdc
ON CHARACTERISTICS				
Zero-Gate-Voltage Drain Current (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0)	I <sub>DSS</sub>	1.0	5.0	mAdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 kHz)	Y <sub>fs</sub>	3000	6000	μmhos
Output Admittance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 kHz)	y <sub>os</sub>	-	50	μmhos
Input Capacitance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>iss</sub>	-	5.0	pF
Reverse Transfer Capacitance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 10 MHz)	C <sub>rss</sub>	-	1.0	pF
Output Capacitance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>oss</sub>	-	2.0	pF

## **COMMON SOURCE CHARACTERISTICS ADMITTANCE PARAMETERS**

 $(V_{DS} = 15 \text{ Vdc}, T_{channel} = 25^{\circ}C)$ 

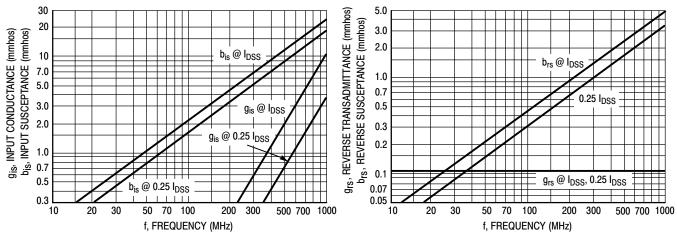


Figure 1. Input Admittance (yis)

Figure 2. Reverse Transfer Admittance (yrs)

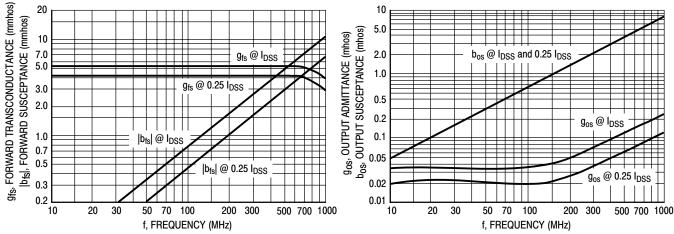


Figure 3. Forward Transadmittance (y<sub>fs</sub>)

Figure 4. Output Admittance (yos)

# COMMON SOURCE CHARACTERISTICS S-PARAMETERS

 $(V_{DS} = 15 \text{ Vdc}, T_{channel} = 25^{\circ}C, Data Points in MHz)$ 

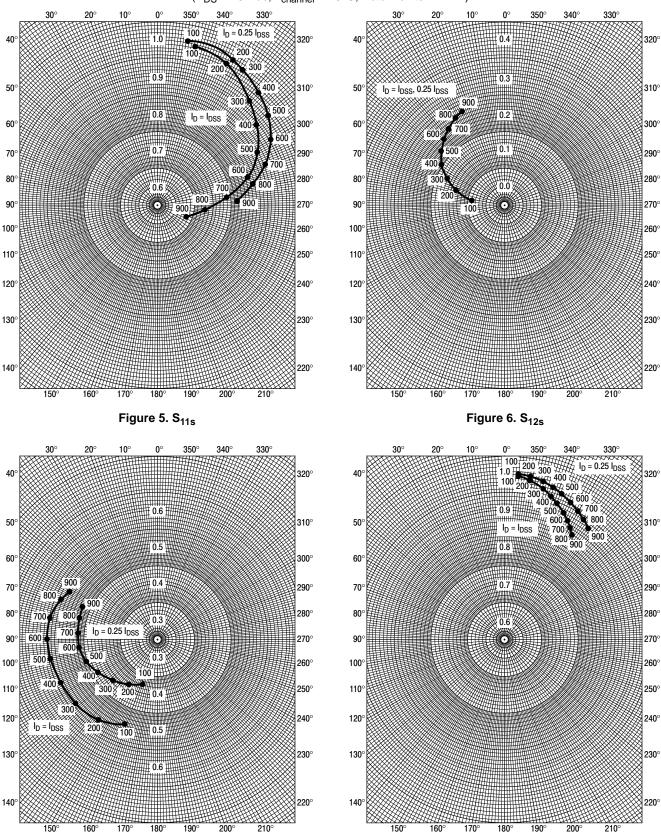


Figure 7. S<sub>21s</sub>

Figure 8. S<sub>22s</sub>

## **COMMON GATE CHARACTERISTICS ADMITTANCE PARAMETERS**

 $(V_{DG} = 15 \text{ Vdc}, T_{channel} = 25^{\circ}C)$ 

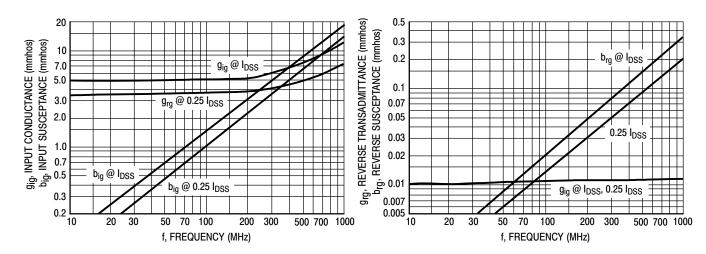


Figure 9. Input Admittance (yig)

Figure 10. Reverse Transfer Admittance (y<sub>rg</sub>)

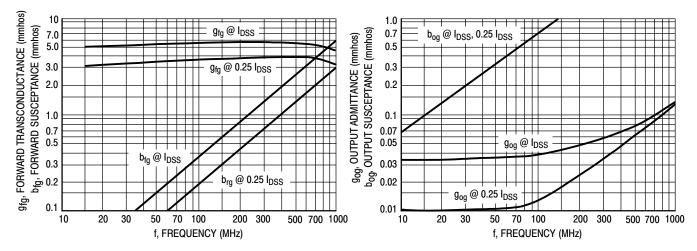
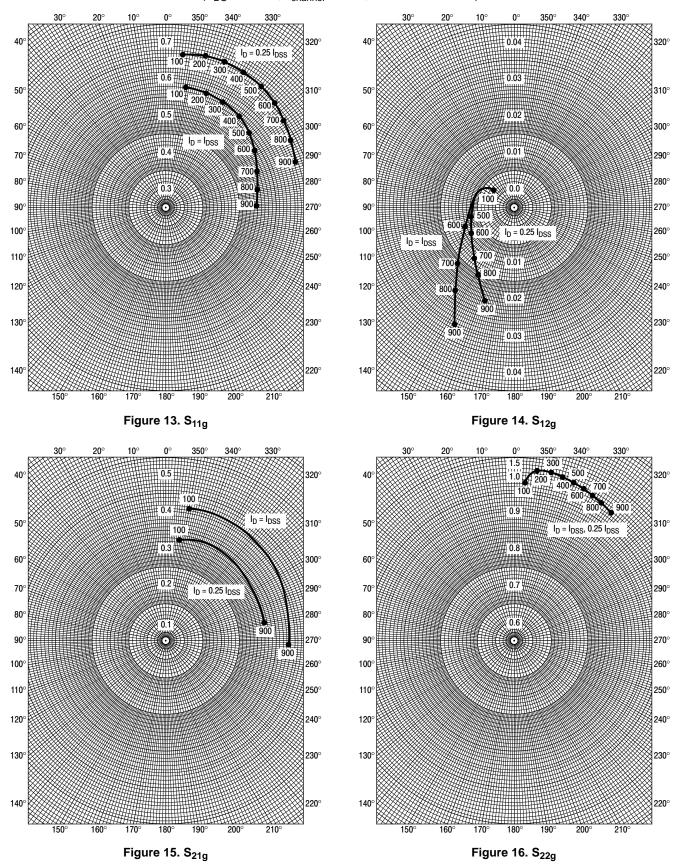


Figure 11. Forward Transfer Admittance (yfg)

Figure 12. Output Admittance (you)

# COMMON GATE CHARACTERISTICS S-PARAMETERS

(V<sub>DS</sub> = 15 Vdc, T<sub>channel</sub> = 25°C, Data Points in MHz)



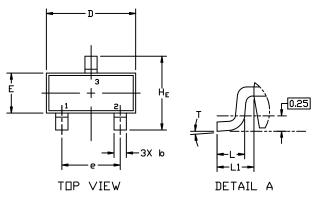




**SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 









#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

# GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

## **STYLES ON PAGE 2**

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<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



## **SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: N PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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